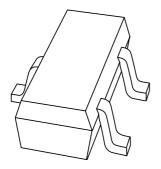
DISCRETE SEMICONDUCTORS

DATA SHEET



BAV70THigh-speed double diode

Product specification Supersedes data of 1997 Dec 19 2004 Feb 04





High-speed double diode

BAV70T

FEATURES

- · Very small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 100V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

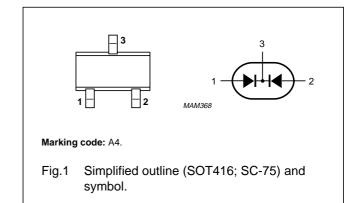
• High-speed switching in e.g. surface mounted circuits.

DESCRIPTION

Two high-speed switching diodes in a common cathode configuration, fabricated in planar technology, in a very small rectangular SMD SOT416 (SC-75) package.

PINNING

PIN	DESCRIPTION	
1	anode 1	
2	anode 2	
3	common cathode	



ORDERING INFORMATION

TYPE	PACKAGE			
NUMBER	NAME	DESCRIPTION	VERSION	
BAV70T	_	plastic surface mounted package; 3 leads SC		

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per diode (ı	Per diode (unless otherwise specified)					
V _{RRM}	repetitive peak reverse voltage		_	100	V	
V _R	continuous reverse voltage		_	100	V	
I _F	continuous forward current	T _s = 90 °C; see Fig.2				
		single diode loaded	_	150	mA	
		both diodes loaded	_	75	mA	
I _{FRM}	repetitive peak forward current		_	500	mA	
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4				
		t = 1 μs	_	4	Α	
		t = 1 ms	_	1	Α	
		t = 1 s	_	0.5	Α	
P _{tot}	total power dissipation	T _s = 90 °C; one diode loaded	_	170	mW	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		_	+150	°C	

High-speed double diode

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CHARACTERISTICS

 T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT	
Per diode					
V _F	forward voltage	see Fig.3			
		I _F = 1 mA	0.715	V	
		I _F = 10 mA	0.855	V	
		I _F = 50 mA	1	V	
		I _F = 150 mA	1.25	V	
I _R	reverse current	see Fig.5			
		V _R = 25 V	30	nA	
		V _R = 75 V	2	μΑ	
		V _R = 25 V; T _j = 150 °C	60	μΑ	
		V _R = 75 V; T _j = 150 °C	100	μΑ	
C _d	diode capacitance	V _R = 0; f = 1 MHz; see Fig.6	1.5	pF	
t _{rr}	reverse recovery time	switching from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7	4	ns	
V _{fr}	forward recovery voltage	switched to $I_F = 10 \text{ mA}$; $t_r = 20 \text{ ns}$; see Fig.8	1.75	V	

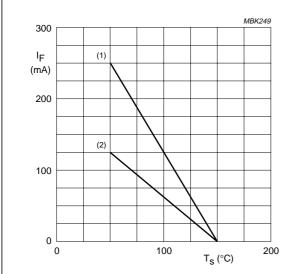
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-s)}	thermal resistance from junction to soldering point	one diode loaded	350	K/W

High-speed double diode

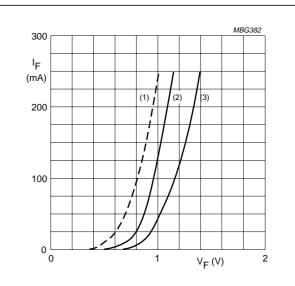
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GRAPHICAL DATA



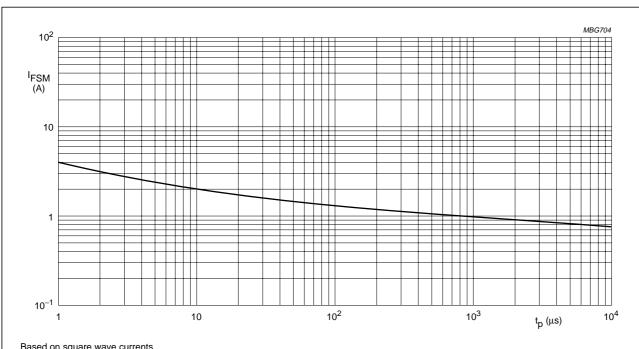
- (1) One diode loaded.
- (2) Both diodes loaded.

Fig.2 Maximum permissible continuous forward current per diode as a function of soldering point temperature.



- (1) $T_i = 150$ °C; typical values.
- (2) $T_i = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



Based on square wave currents.

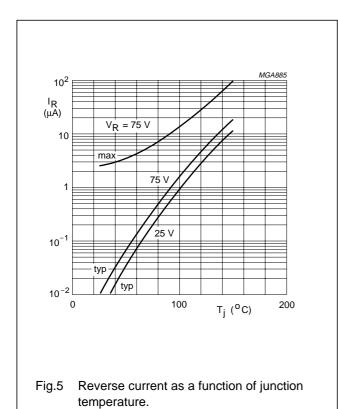
 $T_i = 25$ °C prior to surge.

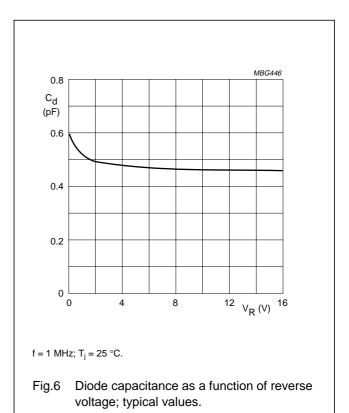
Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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High-speed double diode

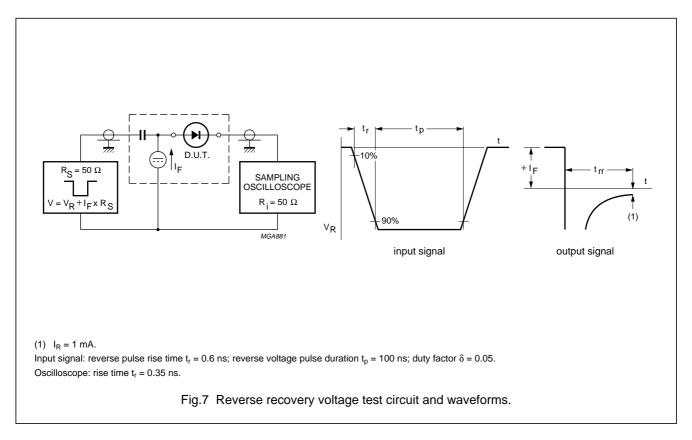
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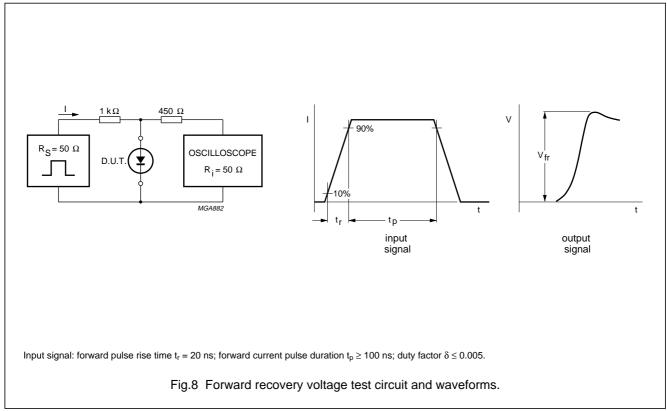




High-speed double diode

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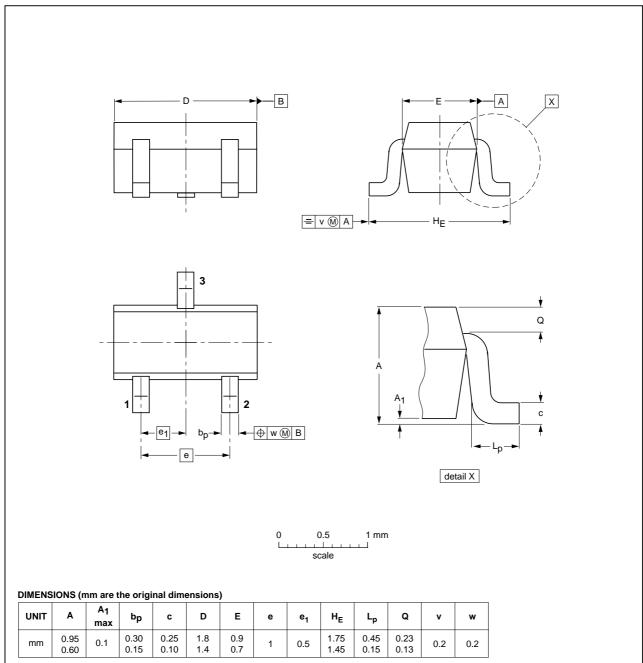
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT416



OUTLINE	DUTLINE REFERENCES EUROPEAN IS			ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT416			SC-75		97-02-28

High-speed double diode

BAV70T

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

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